

7MBR30XKC065-50

IGBT Modules

Power Module(X series)
650V / 30A / PIM

□ **Features**

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant Product

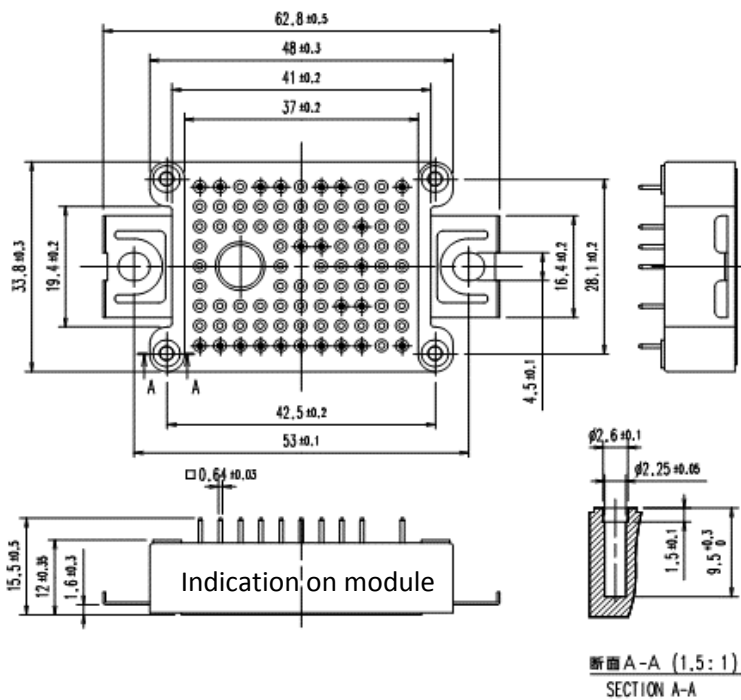
□ **Applications**

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

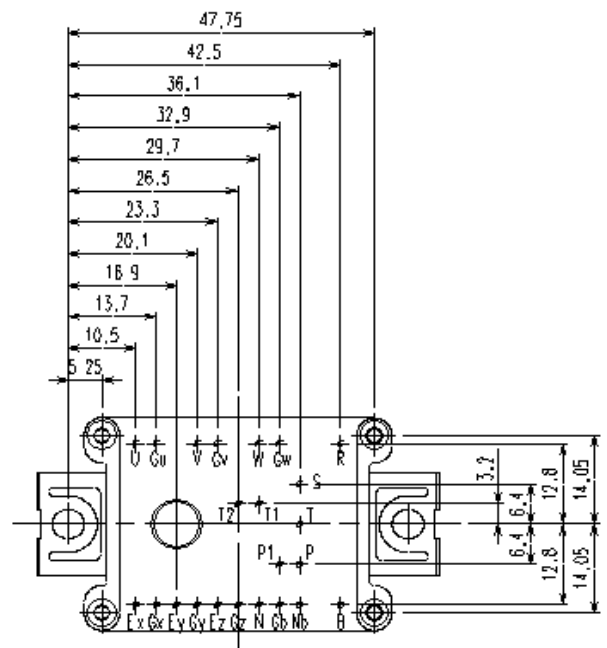
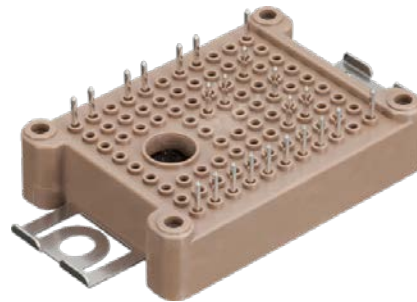
□ **Outline drawing (Unit : mm)**

shows theoretical dimension.

() shows reference dimension.



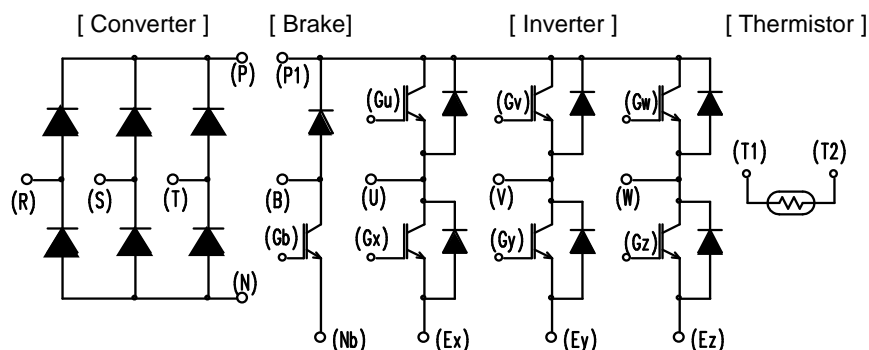
□ **Typical appearance**



Weight: 25 g (typ.)

PIN POSITIONS WITH TOLERANCE $\boxed{\phi} \boxed{0.4}$

□ **Equivalent circuit**



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□ Maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V_{CES}			650	V	
	Gate-Emitter voltage	V_{GES}			± 20	V	
	Collector current	I_C	Continuous	$T_c=100^\circ\text{C}$	30	A	
		I_C pulse	1ms		60		
	Forward current	I_F	Continuous		30		
		I_F pulse	1ms		60		
Collector power dissipation	P_C	1 device		180	W		
Brake IGBT	Collector-Emitter voltage	V_{CES}			650	V	
	Gate-Emitter voltage	V_{GES}			± 20	V	
	Collector current	I_C	Continuous	$T_c=100^\circ\text{C}$	30	A	
		I_C pulse	1ms		60		
Collector power dissipation	P_C	1 device		180	W		
Brake FWD	Forward current	I_F	Continuous		10	A	
		I_{FRM}	1ms		20		
	Repetitive peak reverse voltage	V_{RRM}			650	V	
Converter	Repetitive peak reverse voltage	V_{RRM}			800	V	
	Average output current	I_O	Three-phase full wave rectified	$T_c=80^\circ\text{C}$	30	A	
	Surge current (Non-Repetitive) (*1)	I_{FSM}	$t=10\text{ms}$, Half sine wave form	$T_{vj}=25^\circ\text{C}$	390	A	
				$T_{vj}=150^\circ\text{C}$	340		
I^2t (Non-Repetitive) (*1)	I^2t		$T_{vj}=25^\circ\text{C}$	760	A^2s		
			$T_{vj}=150^\circ\text{C}$	585			
Junction temperature	T_{vj}	Inverter, Brake		175	$^\circ\text{C}$		
		Converter		150			
Operating junction temperature (under switching conditions)	T_{vjop}	Inverter, Brake		175			
		Converter		150			
Case temperature	T_c			125			
Storage temperature	T_{stg}			-40 ~ 125			
Isolation voltage	between terminals and copper base (*2)	V_{iso}	A.C. : 1min.			2500	Vrms
	between thermistor and others (*3)						
Screw torque (*4)	Mounting	-	M4	1.7	N·m		

(*1) T_j : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*4) Recommendable value : Mounting 1.3 ~ 1.7 N·m (M4)

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□ Electrical characteristics (at $T_{vj} = 25^\circ\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units			
			min.	typ.	max.				
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 650\text{V}$	-	-	50	μA			
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}$ $V_{GE} = +20/-20\text{V}$	-	-	100	nA			
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 30\text{mA}$	6.0	6.5	7.0	V			
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 30\text{A}$	$T_{vj}=25^\circ\text{C}$	-	1.50	1.95	V		
			$T_{vj}=25^\circ\text{C}$	-	1.30	1.75			
	$T_{vj}=125^\circ\text{C}$		-	1.45	-				
	$T_{vj}=150^\circ\text{C}$		-	1.50	-				
	$T_{vj}=175^\circ\text{C}$		-	1.55	-				
Internal Gate resistance	r_g	-	-	0	-	Ω			
			Capacitance	C_{ies}	$V_{CE} = 10\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$	-	3.4	-	nF
						C_{oes}	-	0.13	
C_{res}	-	0.05					-		
Gate charge	Q_G	$V_{CC} = 300\text{V}$ $V_{GE} = -15 \rightarrow +15\text{V}$ $I_C = 30\text{A}$	-	240	-	nC			
Forward voltage	V_F (terminal)	$I_F = 30\text{A}$	$T_{vj}=25^\circ\text{C}$	-	2.05	2.50	V		
			$T_{vj}=25^\circ\text{C}$	-	1.85	2.30			
	$T_{vj}=125^\circ\text{C}$		-	1.90	-				
	$T_{vj}=150^\circ\text{C}$		-	1.85	-				
	$T_{vj}=175^\circ\text{C}$		-	1.85	-				
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 300\text{V}$ $I_C, I_F = 30\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 15\ \Omega$	$T_{vj}=25^\circ\text{C}$	-	0.06	-	μs		
			$T_{vj}=125^\circ\text{C}$	-	0.06	-			
			$T_{vj}=150^\circ\text{C}$	-	0.06	-			
			$T_{vj}=175^\circ\text{C}$	-	0.06	-			
	t_r	$V_{CC} = 300\text{V}$ $I_C, I_F = 30\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 15\ \Omega$	$T_{vj}=25^\circ\text{C}$	-	0.02	-			
			$T_{vj}=125^\circ\text{C}$	-	0.03	-			
			$T_{vj}=150^\circ\text{C}$	-	0.03	-			
			$T_{vj}=175^\circ\text{C}$	-	0.03	-			
	$t_{d(off)}$	$V_{CC} = 300\text{V}$ $I_C, I_F = 30\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 15\ \Omega$	$T_{vj}=25^\circ\text{C}$	-	0.16	-			
			$T_{vj}=125^\circ\text{C}$	-	0.18	-			
			$T_{vj}=150^\circ\text{C}$	-	0.19	-			
			$T_{vj}=175^\circ\text{C}$	-	0.19	-			
	t_f	$V_{CC} = 300\text{V}$ $I_C, I_F = 30\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 15\ \Omega$	$T_{vj}=25^\circ\text{C}$	-	0.04	-			
			$T_{vj}=125^\circ\text{C}$	-	0.04	-			
			$T_{vj}=150^\circ\text{C}$	-	0.04	-			
			$T_{vj}=175^\circ\text{C}$	-	0.04	-			
Reverse recovery time	t_{rr}	$V_{CC} = 300\text{V}$ $I_C, I_F = 30\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 15\ \Omega$	$T_{vj}=25^\circ\text{C}$	-	0.07	-			
			$T_{vj}=125^\circ\text{C}$	-	0.11	-			
			$T_{vj}=150^\circ\text{C}$	-	0.12	-			
			$T_{vj}=175^\circ\text{C}$	-	0.14	-			

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Inverter Switching loss (per pulse)	E_{on}	$V_{CC} = 300V$ $I_C, I_F = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.44	-	mJ
			$T_{vj} = 125^\circ C$	-	0.63	-	
			$T_{vj} = 150^\circ C$	-	0.71	-	
			$T_{vj} = 175^\circ C$	-	0.78	-	
	E_{off}	$V_{CC} = 300V$ $I_C, I_F = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.82	-	
			$T_{vj} = 125^\circ C$	-	1.04	-	
			$T_{vj} = 150^\circ C$	-	1.12	-	
			$T_{vj} = 175^\circ C$	-	1.15	-	
	E_{rr}	$V_{CC} = 300V$ $I_C, I_F = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.24	-	
			$T_{vj} = 125^\circ C$	-	0.38	-	
			$T_{vj} = 150^\circ C$	-	0.42	-	
			$T_{vj} = 175^\circ C$	-	0.50	-	
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 650V$	-	-	50	μA	
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0V, \quad V_{GE} = +20/-20V$	-	-	100	nA	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 30A$	$T_{vj} = 25^\circ C$	-	1.50	1.95	V
			$T_{vj} = 25^\circ C$	-	1.30	1.75	
	$V_{CE(sat)}$ (chip)		$T_{vj} = 125^\circ C$	-	1.45	-	
			$T_{vj} = 150^\circ C$	-	1.50	-	
Internal Gate resistance	r_g	-	-	-	0	-	Ω
			-	-	0	-	
Brake Switching time (*1)	$t_{d(on)}$	$V_{CC} = 300V$ $I_C = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.06	-	μs
			$T_{vj} = 125^\circ C$	-	0.06	-	
			$T_{vj} = 150^\circ C$	-	0.06	-	
			$T_{vj} = 175^\circ C$	-	0.06	-	
	t_r	$V_{CC} = 300V$ $I_C = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.02	-	
			$T_{vj} = 125^\circ C$	-	0.03	-	
			$T_{vj} = 150^\circ C$	-	0.03	-	
			$T_{vj} = 175^\circ C$	-	0.03	-	
	$t_{d(off)}$	$V_{CC} = 300V$ $I_C = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.16	-	
			$T_{vj} = 125^\circ C$	-	0.18	-	
			$T_{vj} = 150^\circ C$	-	0.19	-	
			$T_{vj} = 175^\circ C$	-	0.19	-	
	t_f	$V_{CC} = 300V$ $I_C = 30A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 15 \Omega$	$T_{vj} = 25^\circ C$	-	0.04	-	
			$T_{vj} = 125^\circ C$	-	0.04	-	
			$T_{vj} = 150^\circ C$	-	0.04	-	
			$T_{vj} = 175^\circ C$	-	0.04	-	
Reverse current	I_{RRM}	$V_R = 650V$	-	-	50	μA	
Forward voltage	V_F (terminal)	$I_F = 10A$	$T_{vj} = 25^\circ C$	-	1.75	2.20	V
			$T_{vj} = 25^\circ C$	-	1.55	2.00	
	V_F (chip)		$T_{vj} = 125^\circ C$	-	1.50	-	
			$T_{vj} = 150^\circ C$	-	1.50	-	
Reverse current	I_{RRM}	$V_R = 800V$	-	-	50	μA	
			-	-	50	μA	
			-	-	50	μA	
			-	-	50	μA	
Forward voltage	V_{FM}	$I_F = 30A$	terminal	-	1.25	1.70	V
			chip	-	1.05	1.50	
Resistance	R	$T = 25^\circ C$	-	5000	-	Ω	
		$T = 100^\circ C$	465	495	520		
B value	B	$T = 25/50^\circ C$	3305	3375	3450	K	

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

□Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.82	°C/W
		Inverter FWD	-	-	1.50	
		Brake IGBT	-	-	0.82	
		Brake FWD	-	-	1.92	
		Converter Diode	-	-	0.75	
Contact thermal resistance(*1) (1device)	$R_{th(c-f)}$	Inverter IGBT	-	0.75	-	
		Inverter FWD	-	0.92	-	
		Brake IGBT	-	0.78	-	
		Brake FWD	-	0.80	-	
		Converter Diode	-	0.79	-	

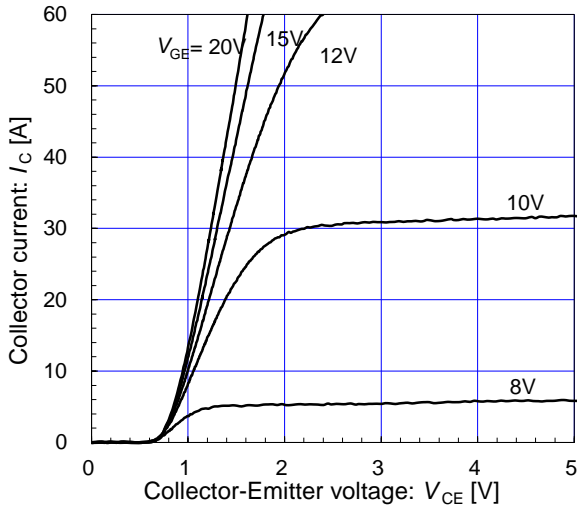
(*1) This is the value which is defined mounting on the additional cooling fin with 1 W/(m·K) thermal grease.

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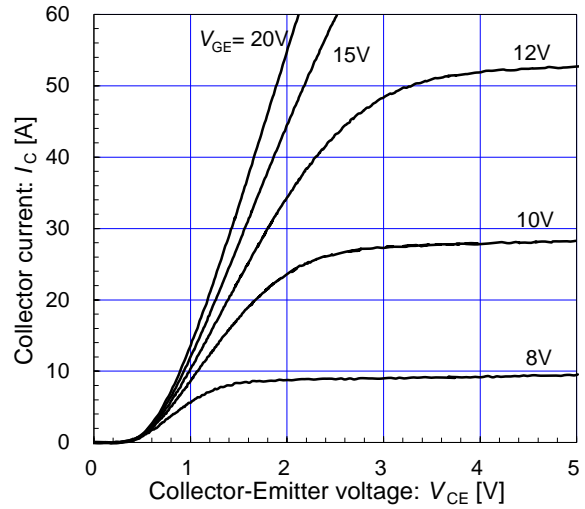
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $T_{vj} = 25^{\circ}\text{C} / \text{chip}$



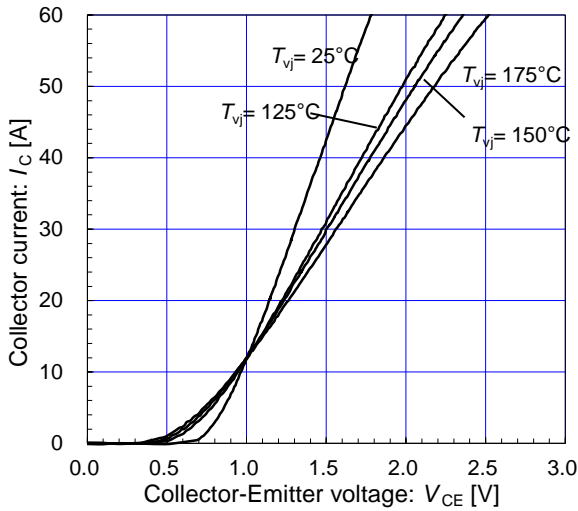
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $T_{vj} = 175^{\circ}\text{C} / \text{chip}$



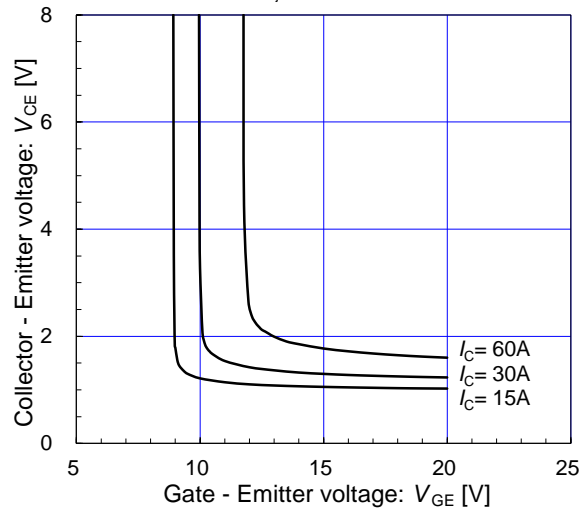
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $V_{GE} = 15\text{V} / \text{chip}$



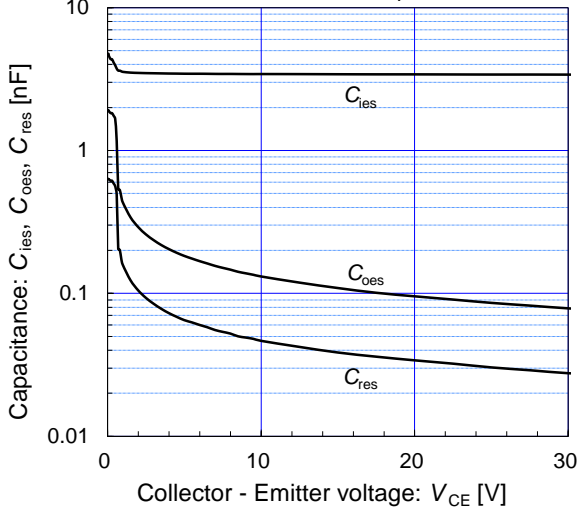
[Inverter]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)
 $T_{vj} = 25^{\circ}\text{C} / \text{chip}$



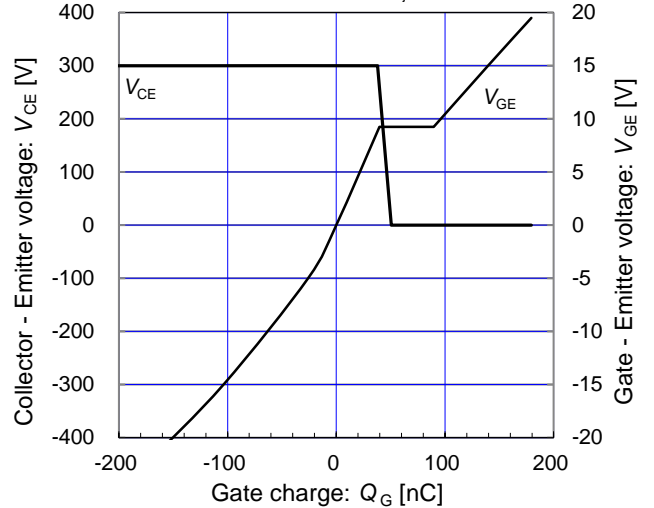
[Inverter]

Capacitance vs. Collector-Emittor voltage (typ.)
 $V_{GE} = 0\text{V}, f = 1\text{MHz}, T_{vj} = 25^{\circ}\text{C}$



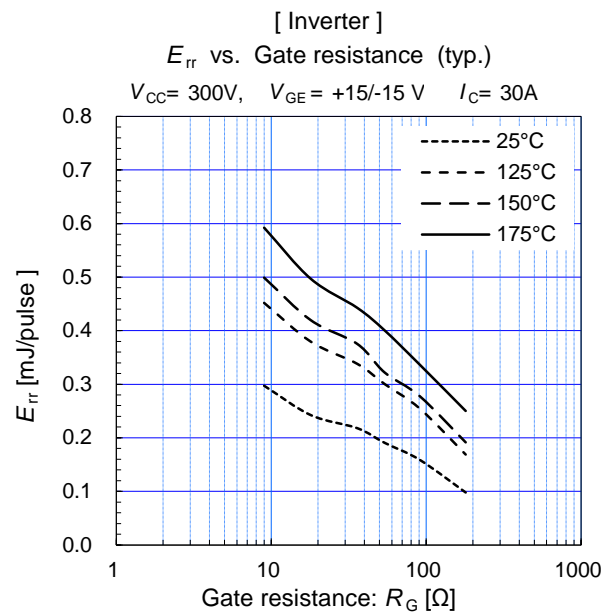
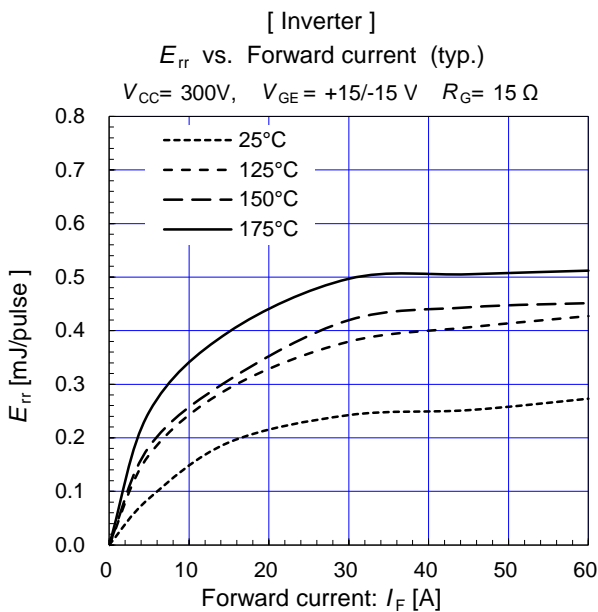
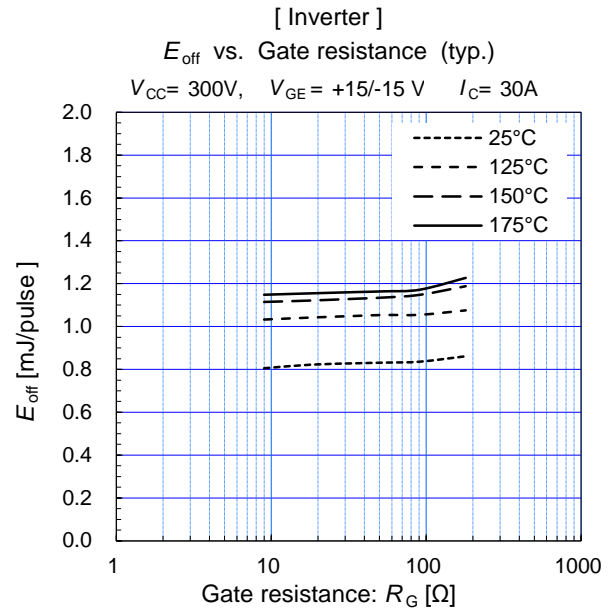
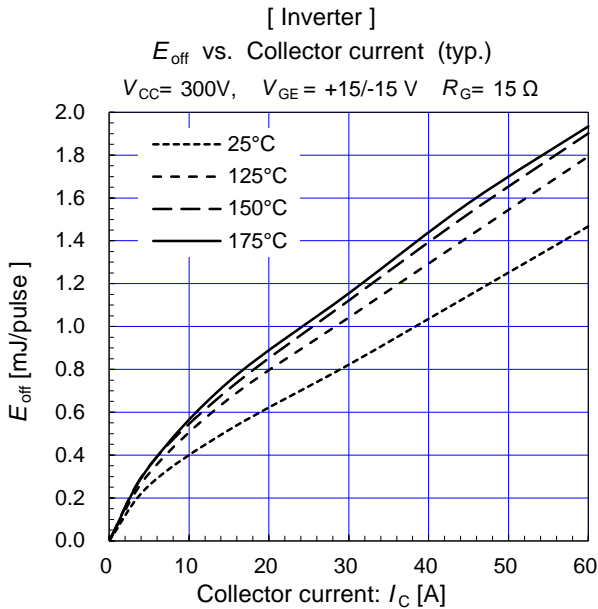
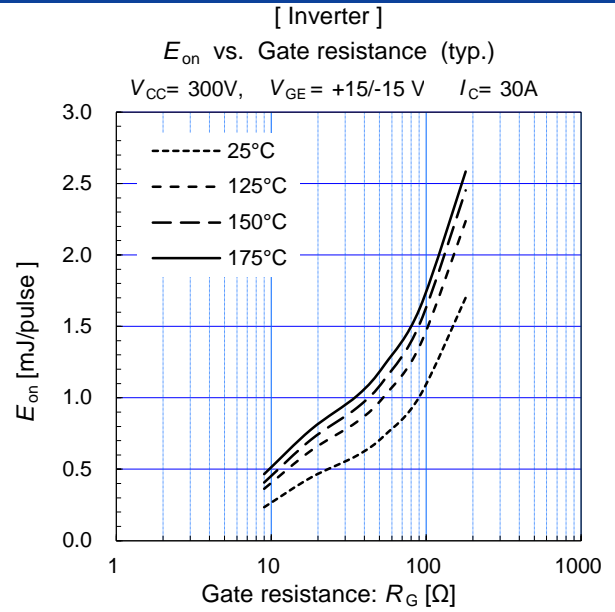
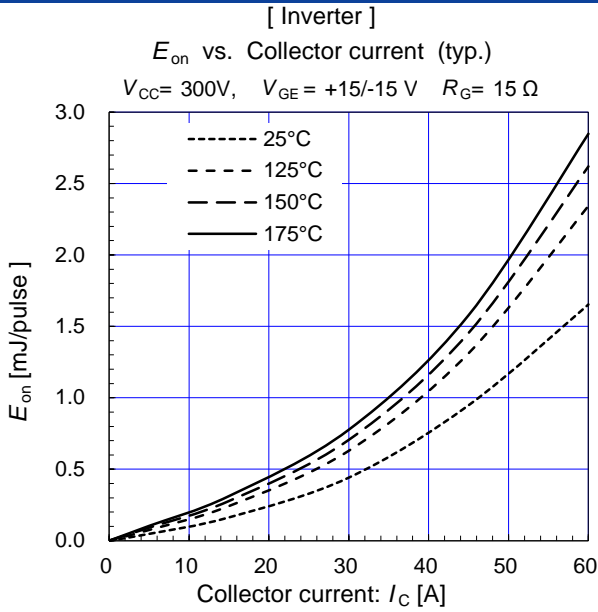
[Inverter]

Dynamic Gate charge (typ.)
 $V_{CC} = 300\text{V}, I_c = 30\text{A}, T_{vj} = 25^{\circ}\text{C}$



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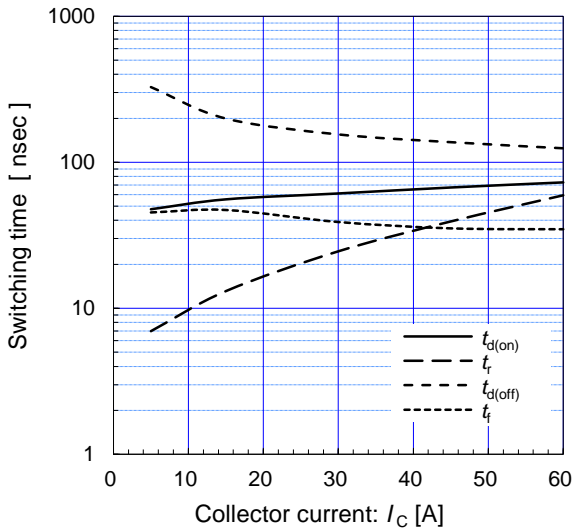
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[Inverter]

Switching time vs. Collector current (typ.)

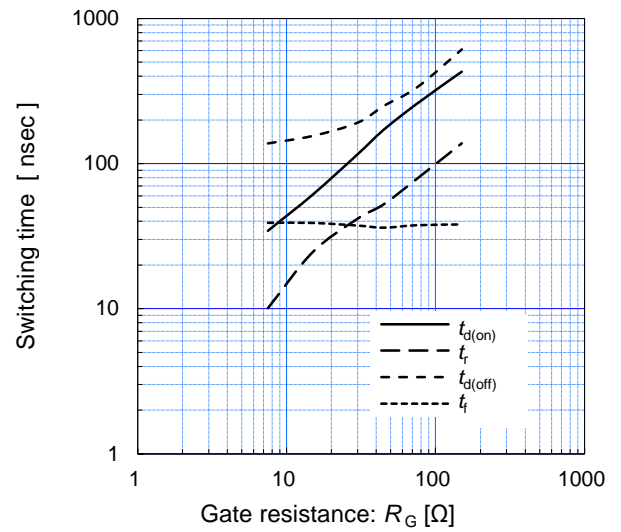
$V_{CC}=300V, R_G=15\Omega, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

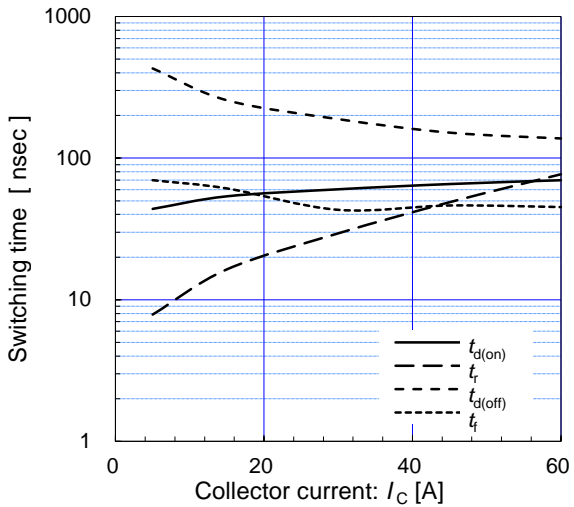
$V_{CC}=300V, I_C=30A, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

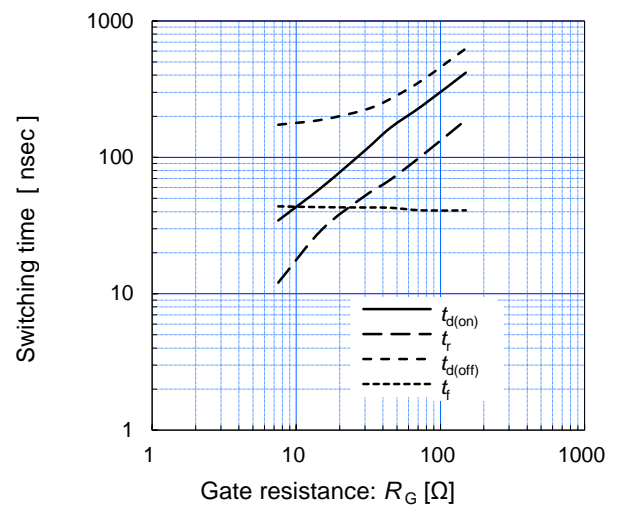
$V_{CC}=300V, R_G=15\Omega, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

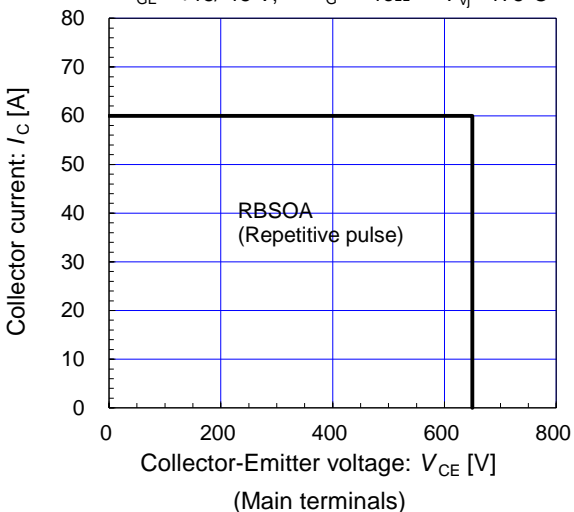
$V_{CC}=300V, I_C=30A, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Reverse bias safe operating area (max.)

$V_{GE}=+15/-15V, R_G \ge 15\Omega, T_{vj}=175^\circ C$

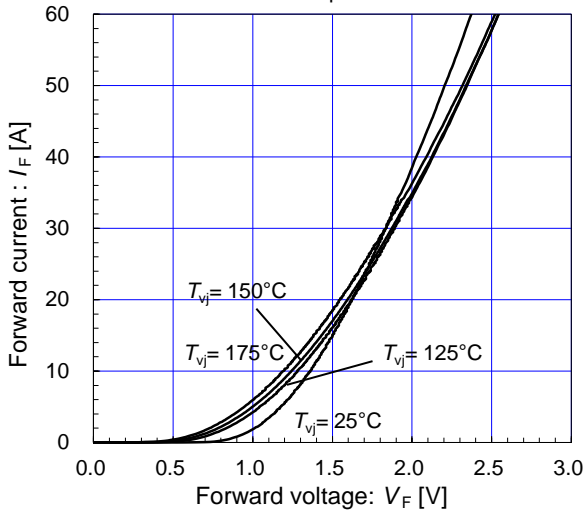


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[Inverter]

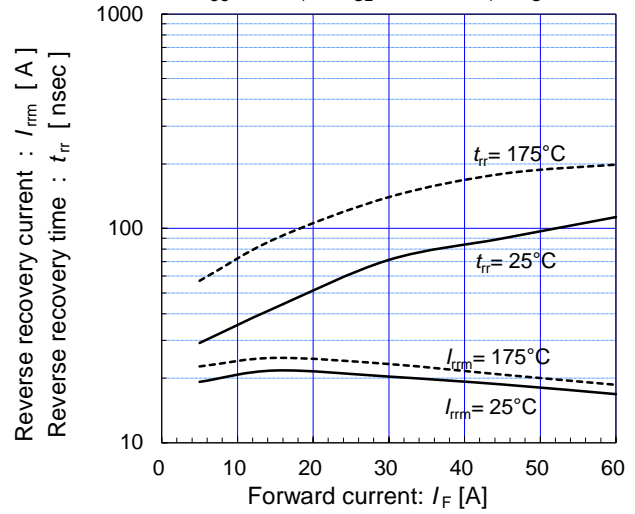
Forward current vs. Forward voltage (typ.)
chip



[Inverter]

Reverse recovery characteristics (typ.)

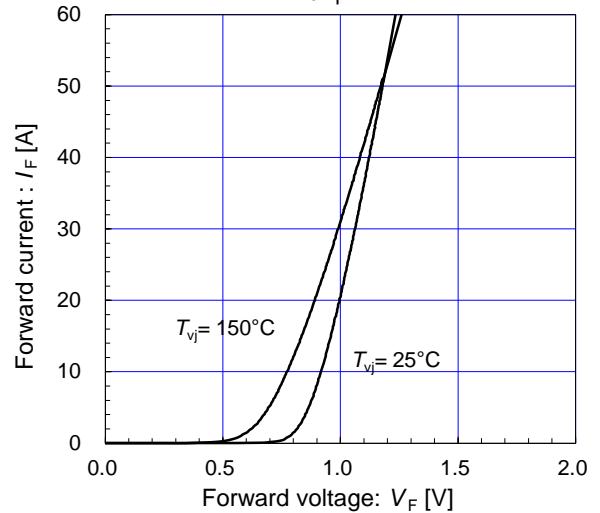
$V_{CC} = 300V, V_{GE} = +15/-15V, R_G = 15\Omega$



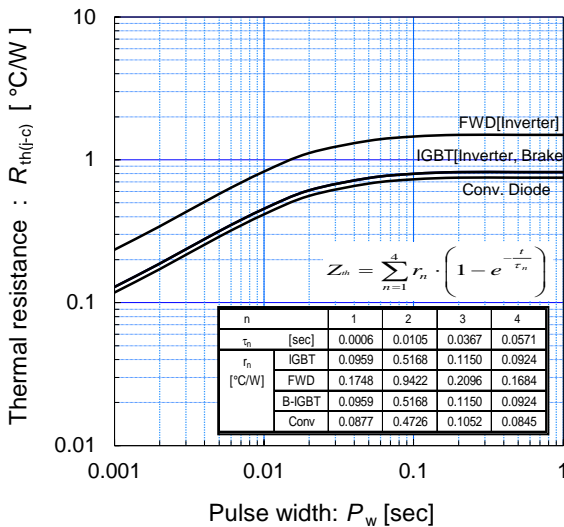
[Converter]

Forward current vs. Forward voltage (typ.)

chip

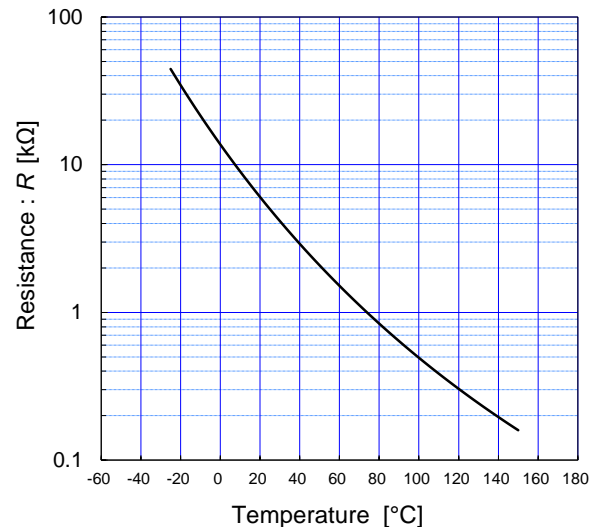


Transient thermal resistance (max.)

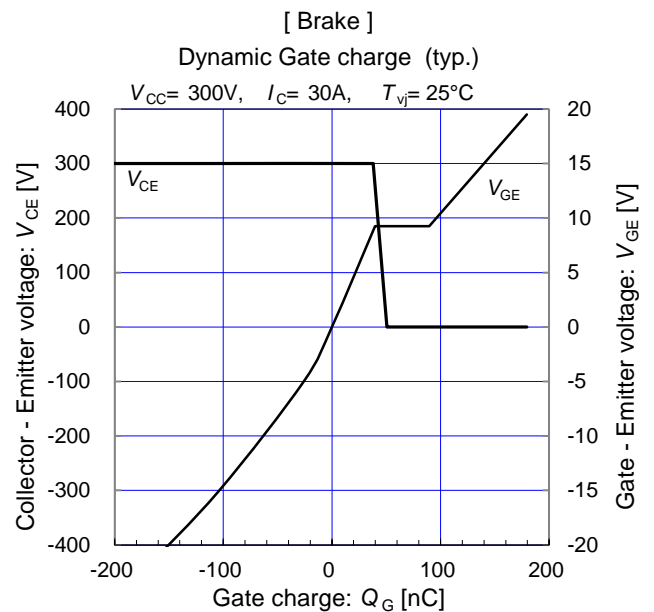
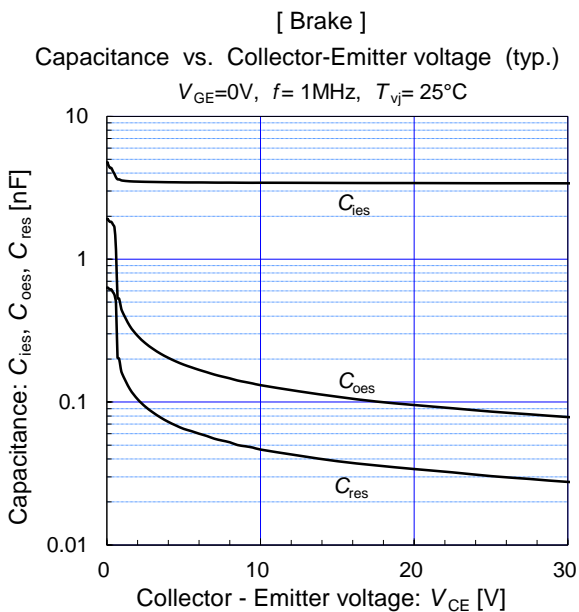
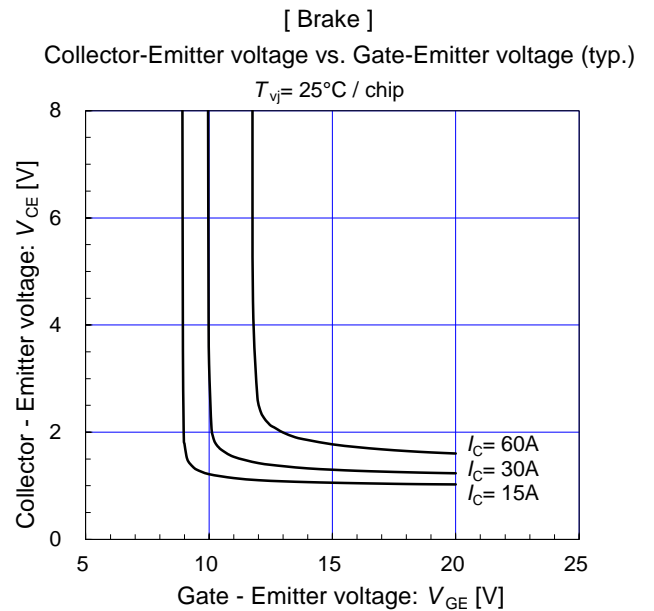
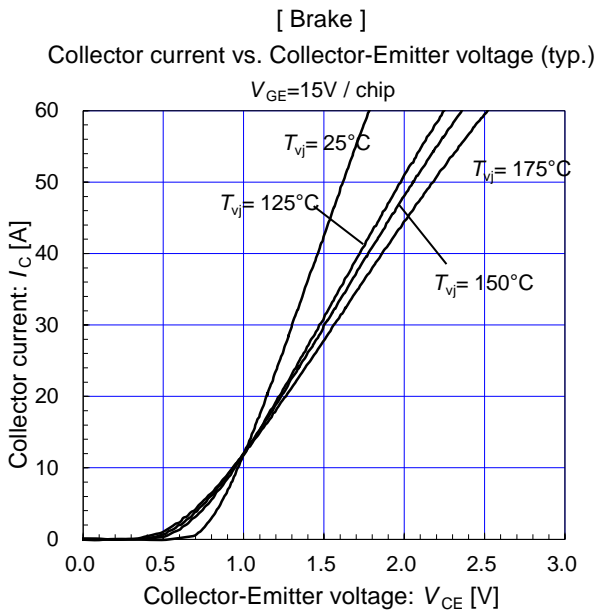
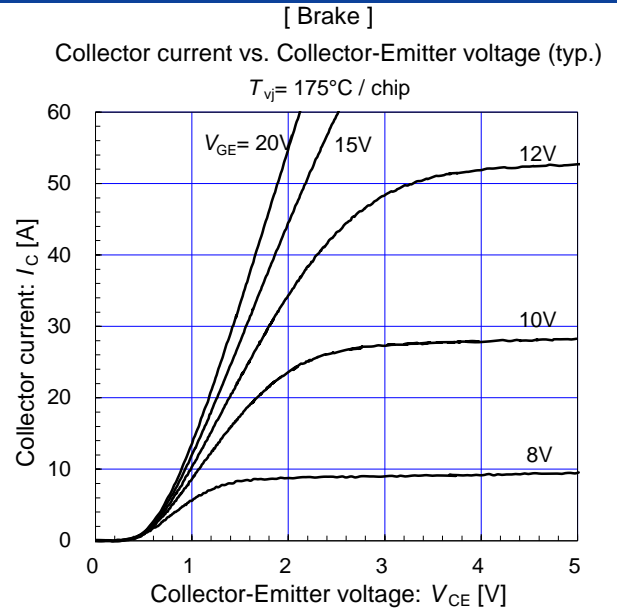
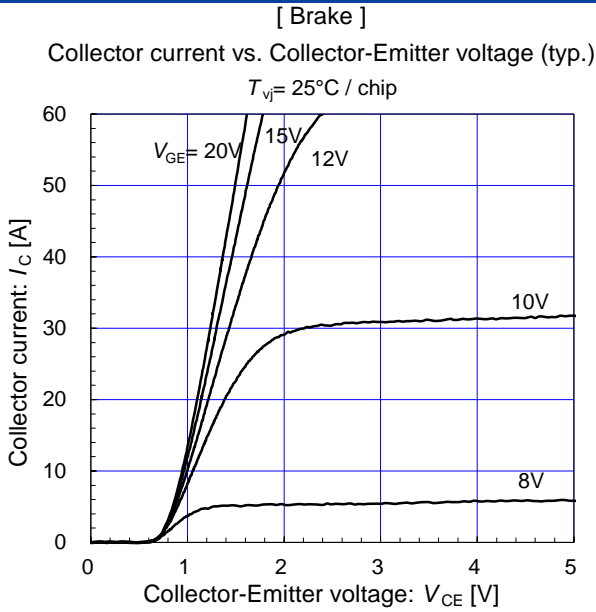


[Thermistor]

Temperature characteristic (typ.)



7MBR30XKC065-50



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IGBT Modules

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